

Run 42998, EVENT 2691  
26-APR-1998 01:33  
Source: Run Data Pol: R  
Trigger: Energy Hadron WAB  
Beam Crossing 1192559971

**b/c-tagging**

**Lecture 2**

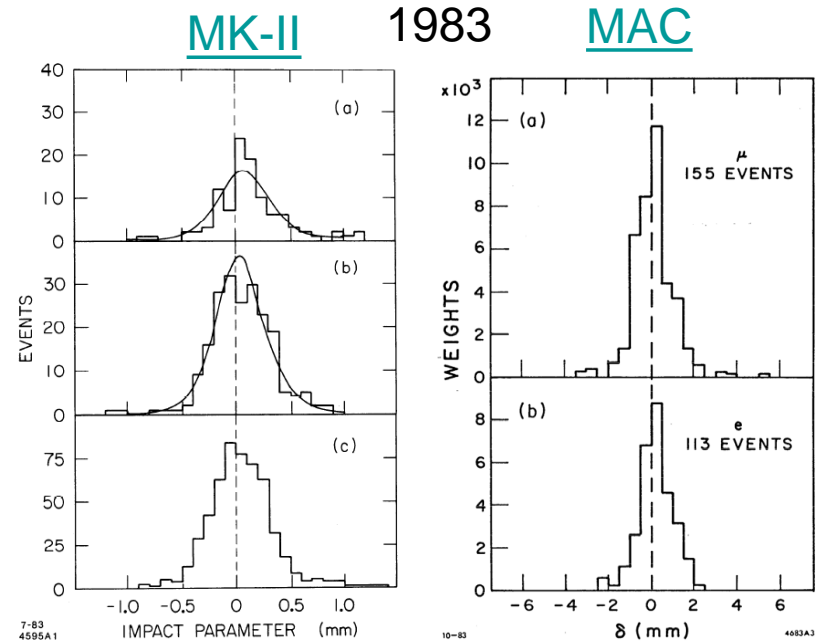
**Topics on Detectors  
for b/c Tagging**

**Su Dong**



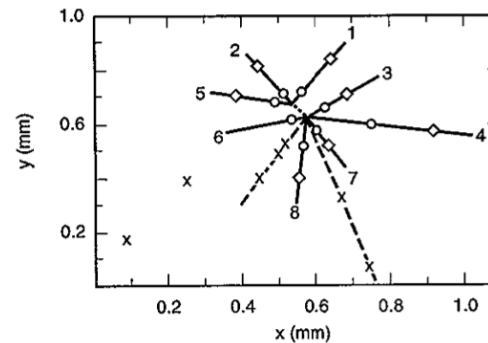
# Vertex Detector Chronology: 80s

- Vertex drift chambers @  $e^+e^-$  colliders
  - $\tau$ , charm, b lifetime: MK-II, MAC, HRS, DELCO @PEP, TASSO, JADE@PETRA, CLEO@CESR, ARGUS@DORIS
  - Lifetime b-tag: TASSO
- Various detector types @ fixed target
  - All aimed at charm lifetime measurements
  - Silicon strip: ACCMOR (+CCD)@CERN, E691@FNAL, ...
  - Emulsion, Bubble chambers ...



$$\tau_B = 1.2 \pm 0.4 \pm 0.3$$

$$\tau_B = 1.8 \pm 0.6 \pm 0.4$$



NA32  
with  
CCD

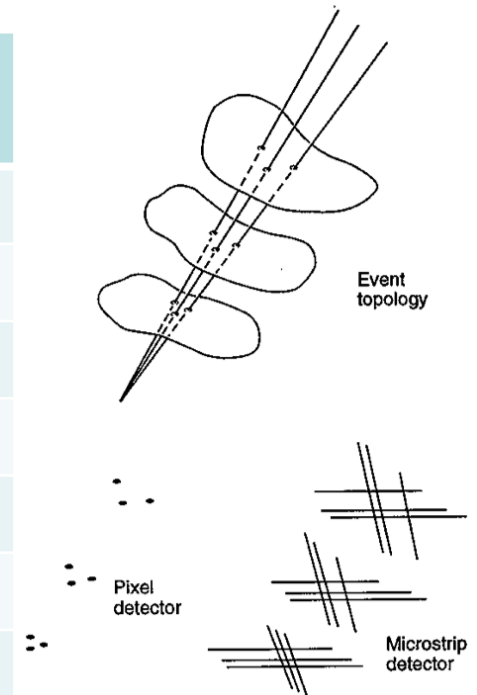
# Vertex Detector Chronology: 90s

- $e^+e^-$  @ SLC/LEP
  - Si strip: MK-II, ALEPH, DELPHI, L3, OPAL
  - CCD pixel: SLD
  - $\tau$ , b lifetime and B mixing
  - **Lifetime b-tag**:  $R_b$ , b asymmetry, QCD b jets, Higgs search...
  - **Lifetime c-tag**:  $R_c$ , c asymmetry (SLD only)
- $p\bar{p}$  @ Tevatron
  - Silicon strip detectors at CDF, D0
  - b lifetime and B mixing
  - **Lifetime b-tag**: top quark, Higgs search...
- Fixed target
  - Si strip: E791, FOCUS @FNAL... more charm lifetime

# Vertex Detectors @ LHC

New pixel era: ATLAS/CMS instrumented with **active** hybrid pixels. Evolution compared to SLD.

Experiment /detector	Pixel type	Year	#pixels	Pixel size ( $\mu\text{m}$ ) (r $\phi$ / z /depth)
<a href="#">SLD VXD2</a>	CCD	1992	120M	22 x 22 x 20
<a href="#">SLD VXD3</a>	CCD	1996	307M	20 x 20 x 20
<a href="#">ATLAS Pixel</a>	hybrid	2008	80M	50 x 400 x 250
<a href="#">CMS Pixel</a>	hybrid	2008	66M	100 x150 x 285
<a href="#">ATLAS IBL</a>	hybrid	2015	12M	50 x 250 x 200
<a href="#">CMS Phase1</a>	hybrid	2017	124M	100 x150 x 200
<a href="#">ATLAS ITk</a>	hybrid	2025	4886M	50 x 50 x 100-200 25 x 100
<a href="#">CMS Phase2</a>	hybrid	2025	1947M	50 x 50 x 100-150 25 x 100

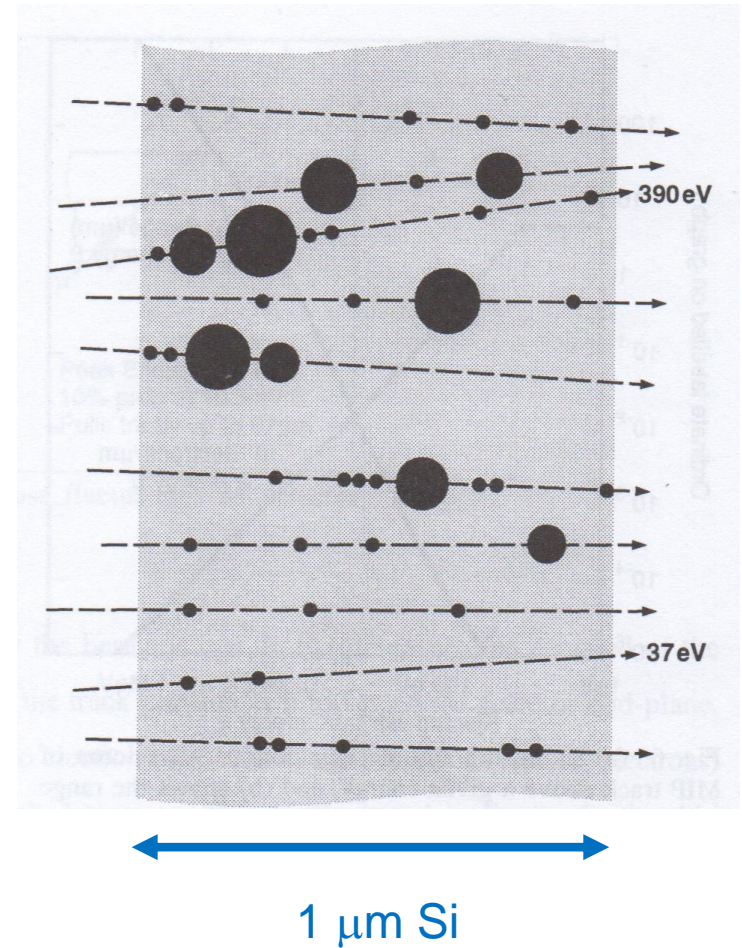
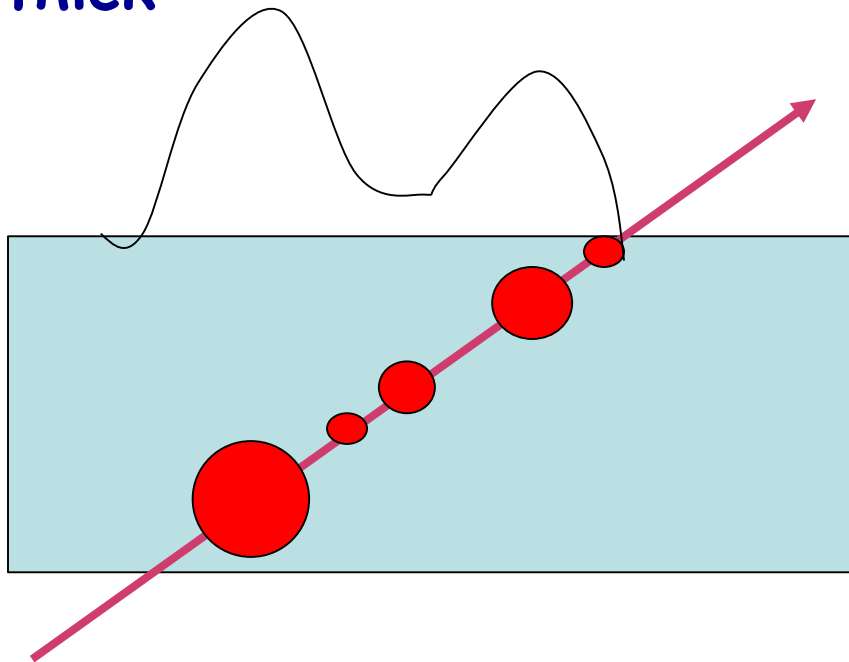




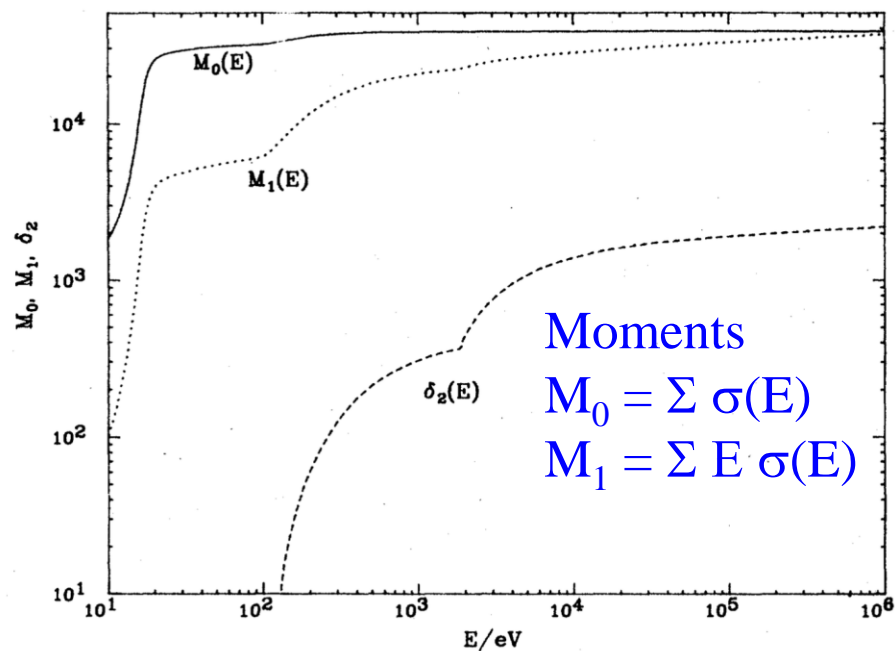
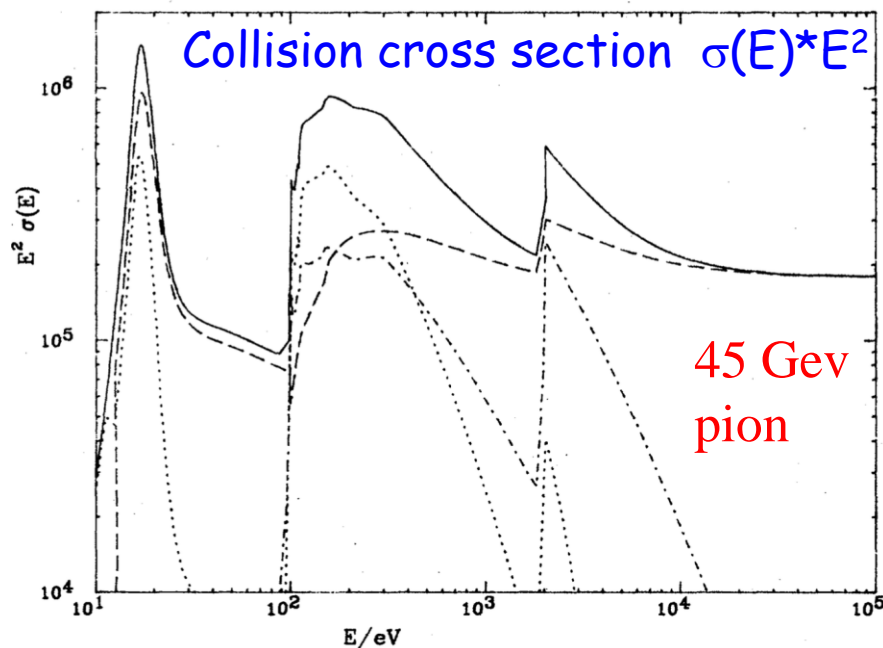
# Charged Particle Ionization in Silicon

# Charged Particle Ionization

Ionization fluctuation is the main culprit of resolution degradation at inclined angle, especially when Si is thick



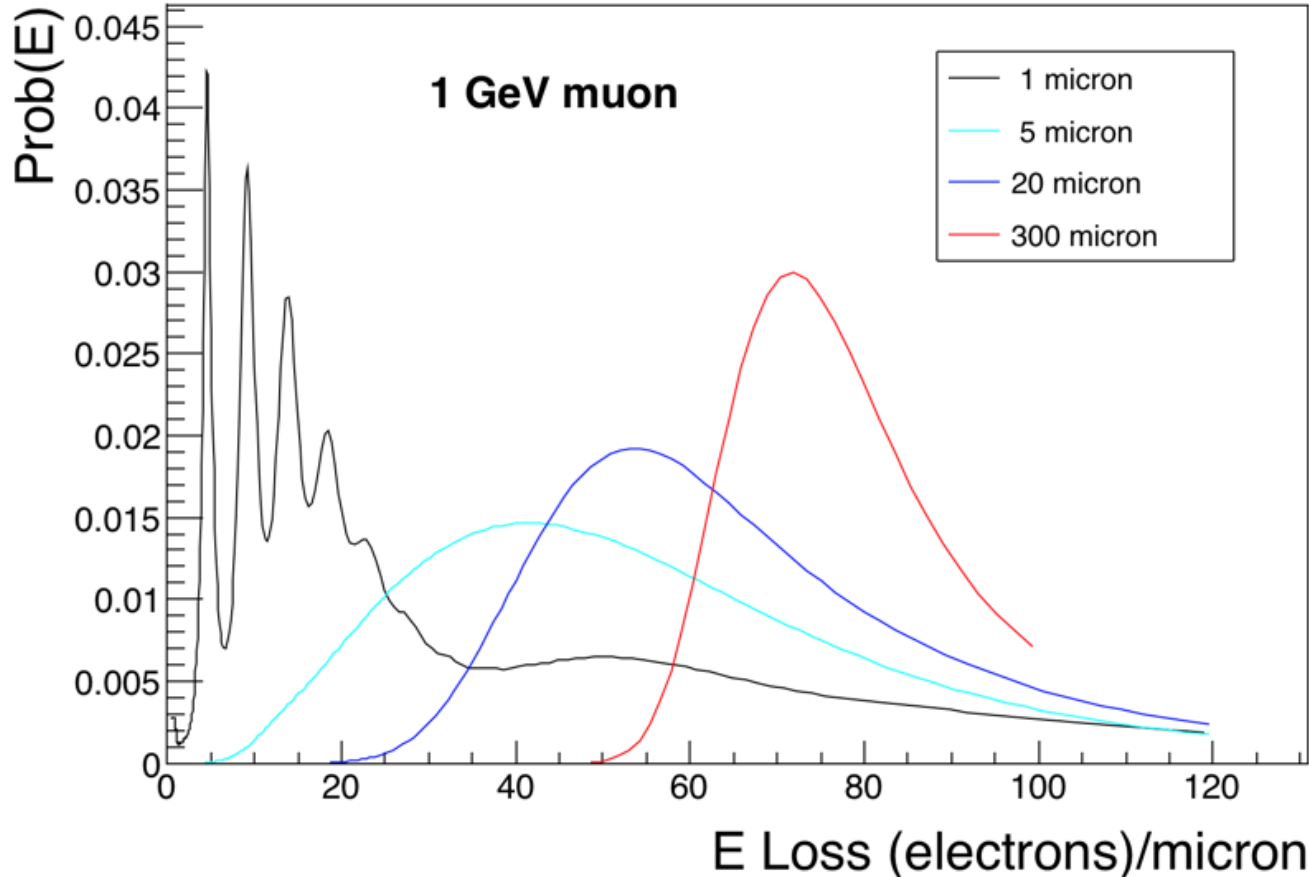
# Atomic Collisions in Silicon



- ~4 collisions per  $\mu\text{m}$  but mostly very low loss (~17eV)
- Total E loss and fluctuation driven by the sporadic large E loss collisions.

# $dE/dx$ is a misleading concept

$dE/dx$  spectrum



Ionization loss spectrum is far from being scalable to different thicknesses as the naïve term  $dE/dx$  might suggest.

For thin Si, it is not Landau



# Bichsel Model in ATLAS Simulation

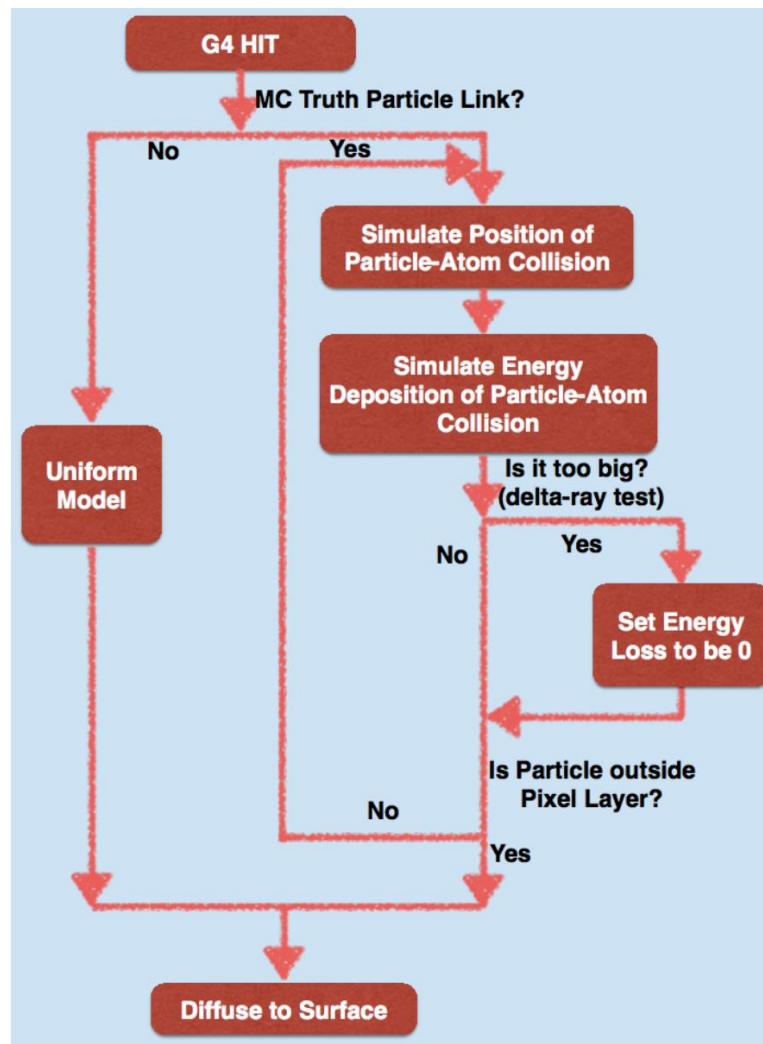
Implementation in ATLAS G4 simulation based on single atomic collision spectrum in Bichsel's COV program.

- Running COV at a few specific  $\beta\gamma$  points to store spectra in numerical tables.
- Individual track hits interpolate to arbitrary  $\beta\gamma$  to generate single atomic collision energy loss
- E-loss Spectrum cuts off at G4  $\delta$ -ray threshold. G4 simulates  $\delta$ -ray explicitly as separate particle.
- Control options to group many collisions  $\ll$  detector resolution together for collective ionization electron diffusion and charge collection to save CPU time.

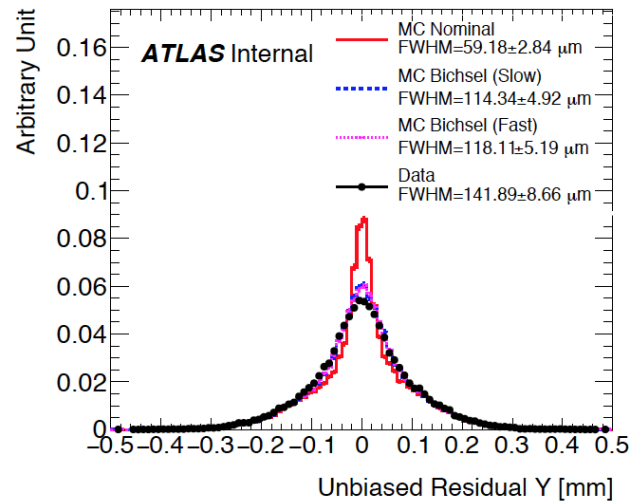
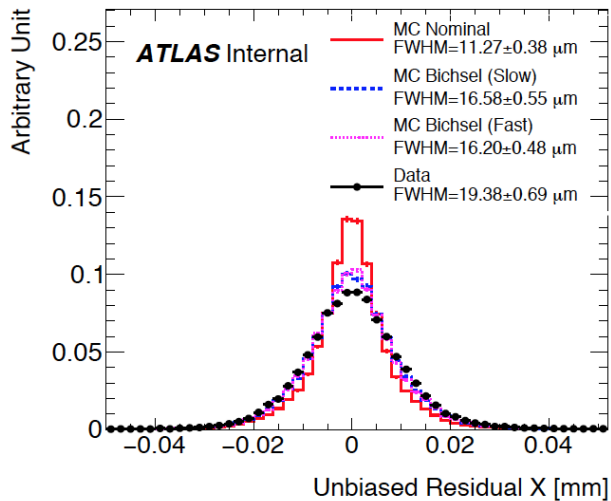
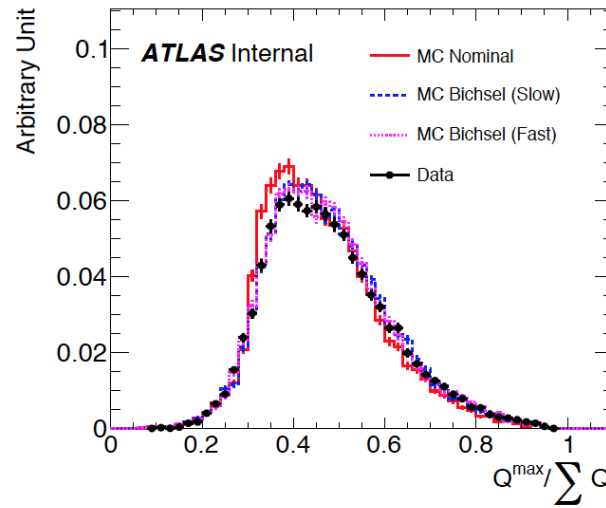
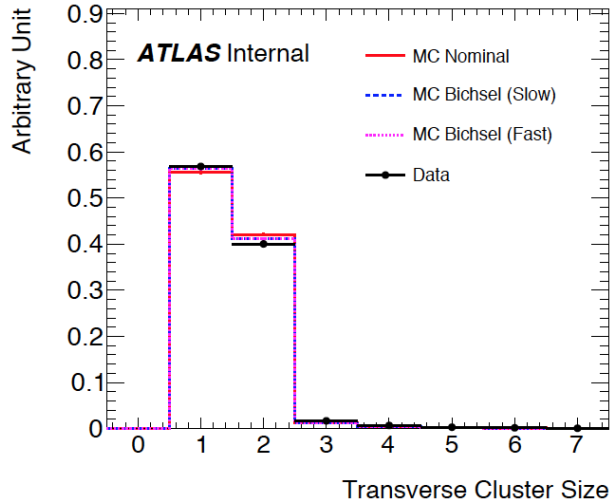
[Q.Zeng Stanford Ph.D thesis: [CERN-thesis-2017-124](#) Appendix A]

# Bichsel Model in ATLAS

- Default ATLAS implementation of Bichsel model only for  $\beta\gamma > 0.7$
- Would have been easier to extend to low  $\beta\gamma$  if grid was done in  $dE/\beta\gamma$  - possible future improvements.
- ATLAS G4  $\delta$ -ray cut default = 117 KeV



# Improvements for ATLAS



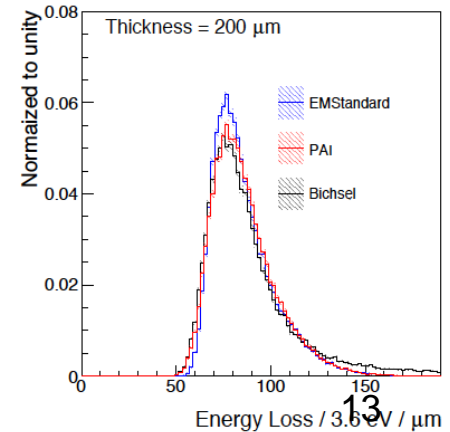
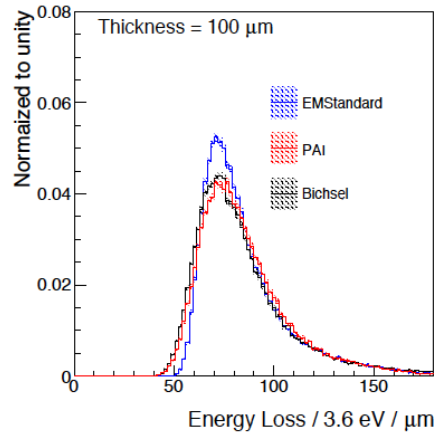
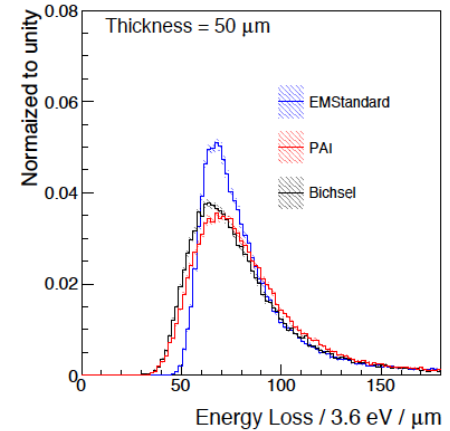
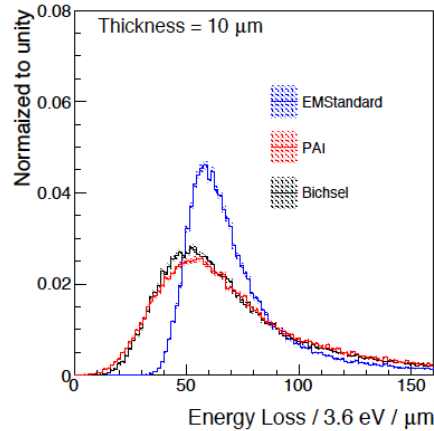
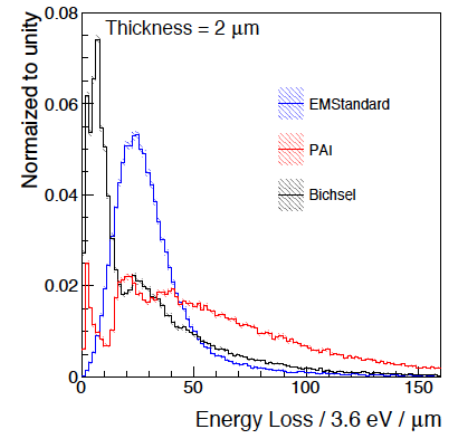
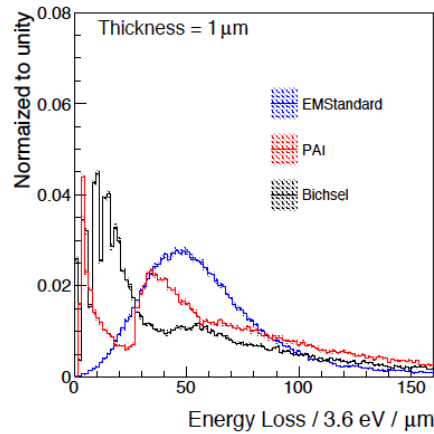
Bichel  
model  
became  
default  
digitization  
in release  
21

# Bichsel Model in Allpix

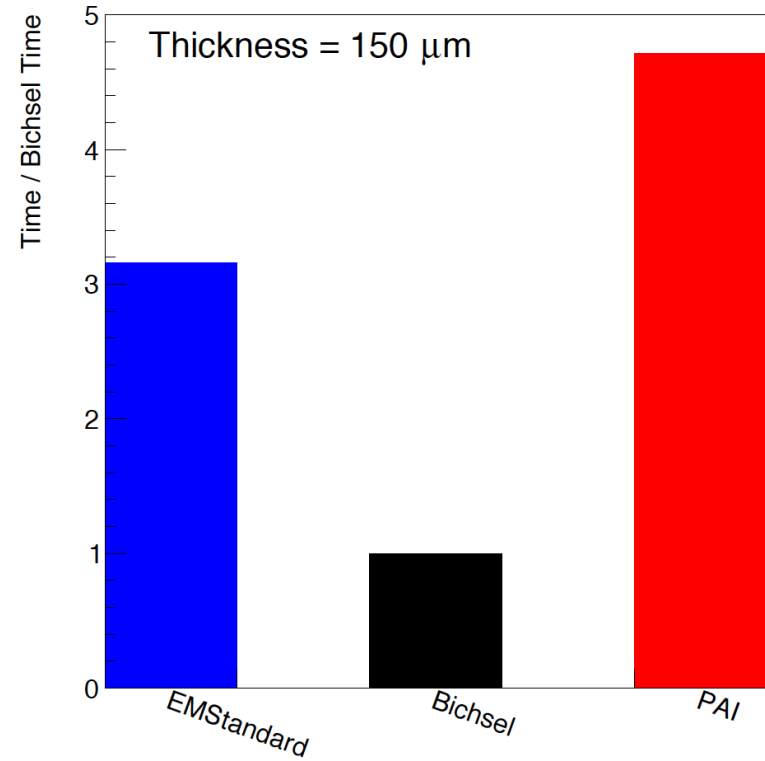
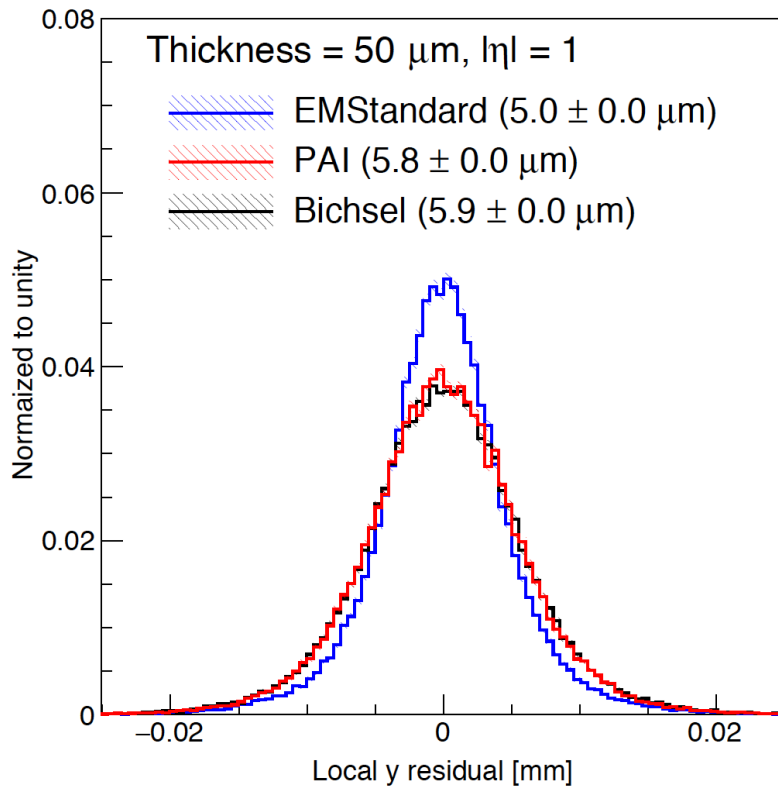
- Work done by Fuyue Wang, Ben Nachman, Maurice Garcia-Sciveres (LBNL)
- Converted COV (Fortran) to C++
- Embedded in Allpix simulation/reconstruction framework as a generic test beam utility  
[Temporary repository (contact Ben Nachman):  
<https://github.com/bnachman/Bichsel> ]
- Some plotting routines to be converted to C++ still.
- Code to dump COV spectrum grid to be converted.
- Compared Bichsel model with G4 EMstandard and PAI models:

# Comparison with G4

- **EMStandard** quite far off for thin silicon
- **PAI** came close but single shell approximation exposed for very thin silicon

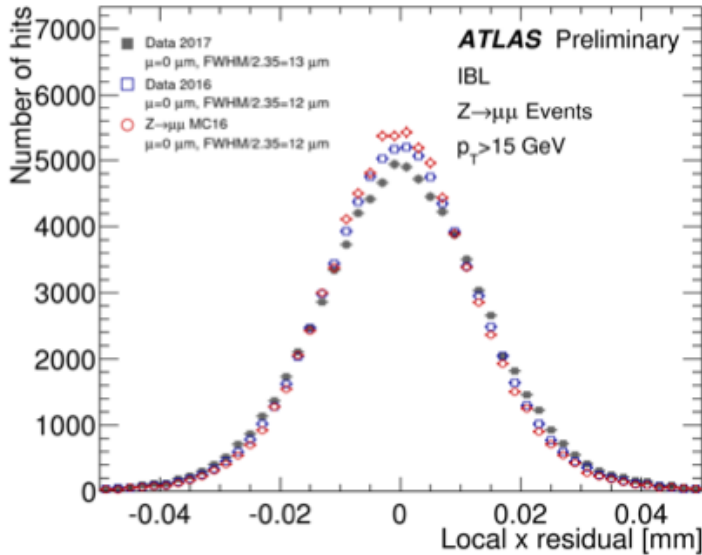


# Comparison with G4

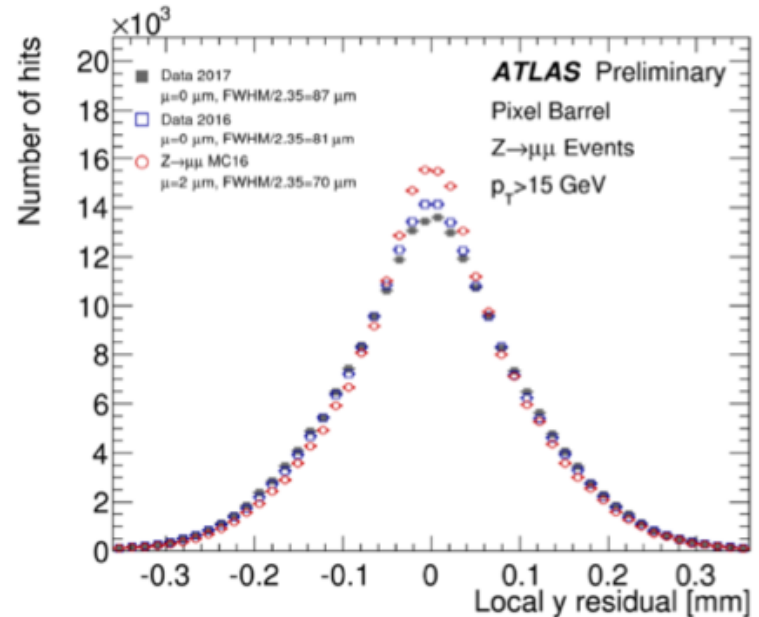


For all practical purposes PAI is good enough but slow

# Spatial Resolution



$r\phi$ : IBL = 13 $\mu\text{m}$



Z: B-layer=87 $\mu\text{m}$


General lesson for detector design:

- Avoid large entrance angle geometry
- Use thin sensors if possible

# References

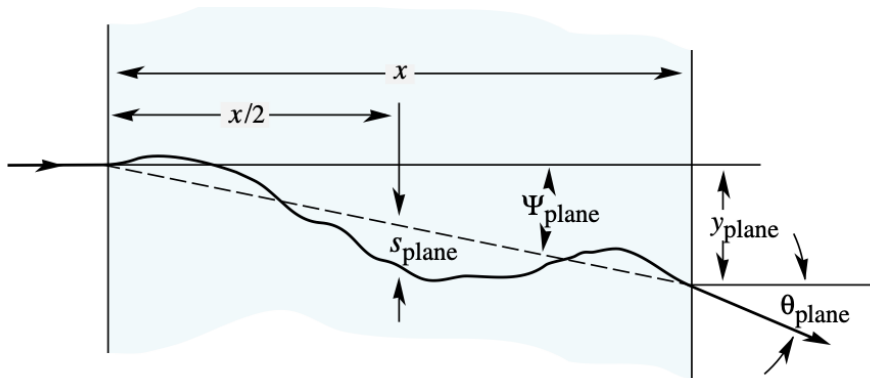
- References for more details on silicon detector principles
  - Chris Damerell: Lectures at SLAC Summer Institute (1995) "Vertex Detectors: the state of art and future prospects" RAL-P-95-008
  - Norbert Wermes: Lectures at SLAC Summer Institute (2016): "Tracking Detectors" [[1](#)][[2](#)]



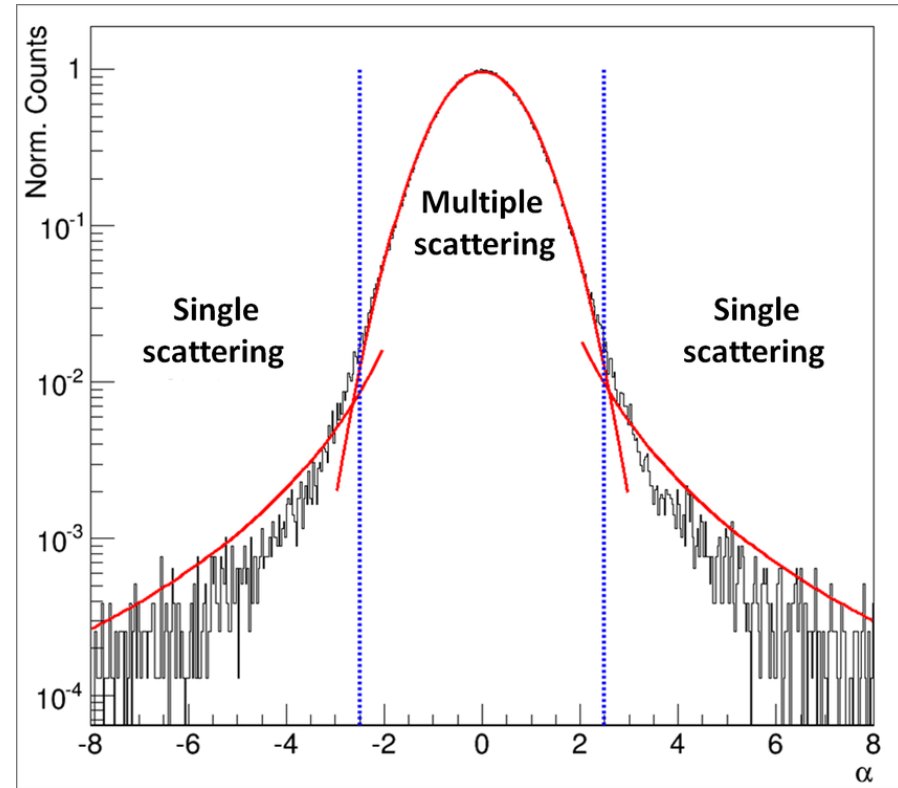


# Multiple Scattering and Material

# Multiple Scattering

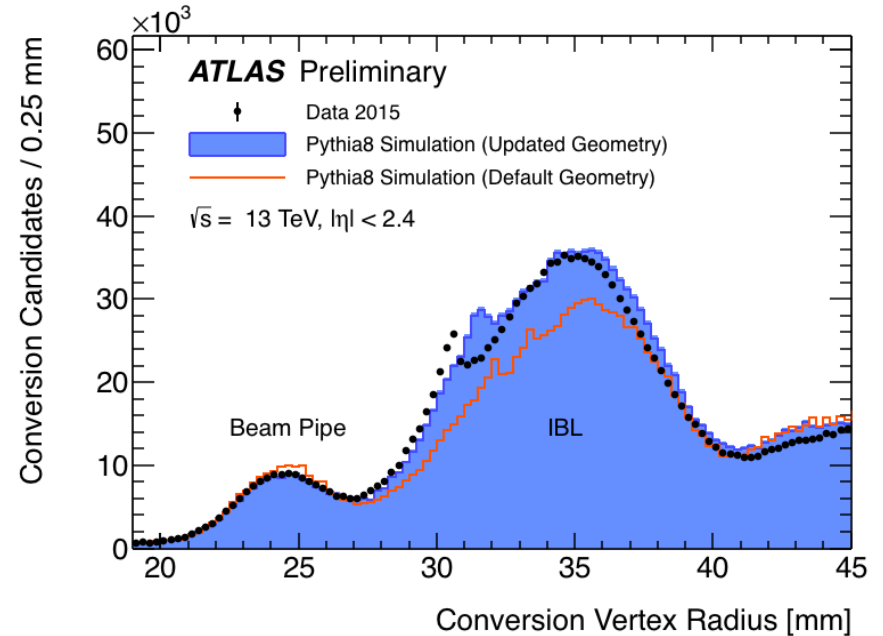
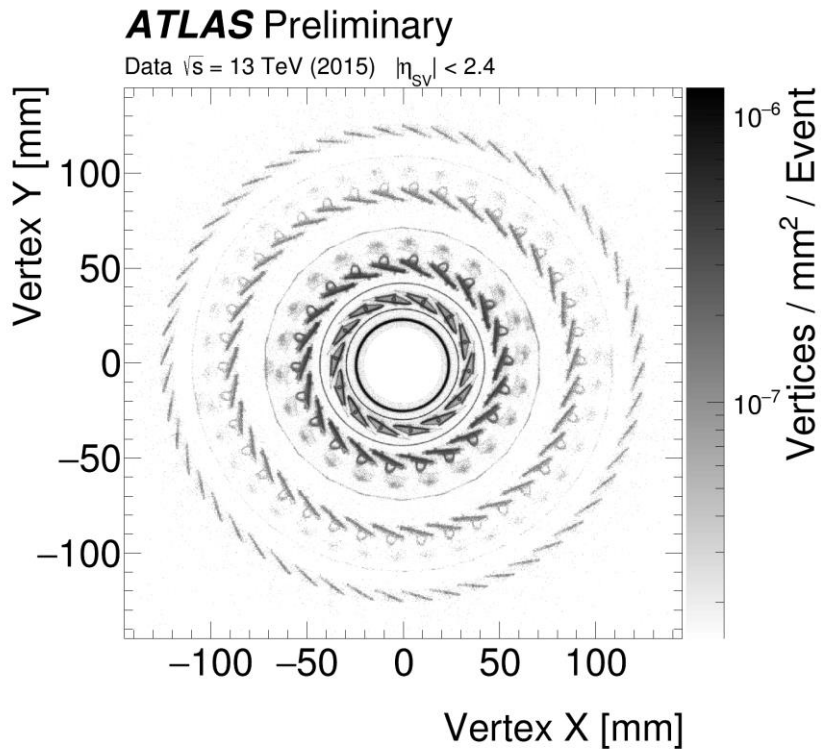


Be aware Gaussian approximations. Tails need to use Moliere scattering (G4)



$$\theta_0 = \frac{13.6 \text{ MeV}}{\beta c p} z \sqrt{\frac{x}{X_0}} \left[ 1 + 0.088 \log_{10} \left( \frac{x z^2}{X_0 \beta^2} \right) \right]$$

# Material Mapping



**Hadronic  
interactions**

# Material notes

- Try to avoid large entrance angle geometry if possible
- Same weight of material can have very different  $X/X_0$  between different material
  - watch out for gold !